

DIGITRON SEMICONDUCTORS

SC260, SC260()3, SC261(MAC261) SERIES

THYRISTORS

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).

Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Repetitive Peak Off-State Voltage ($T_C = -40^\circ\text{C}$ to $+115^\circ\text{C}$) SC260B, SC260B3, SC261B (MAC261B) SC260D, SC260D3, SC261D (MAC261D) SC260E, SC260E3, SC261E (MAC261E) SC620M, SC260M3, SC261M (MAC261M)	V_{DRM}	200 400 500 600	Volts
RMS On-State Current	$I_{\text{T(RMS)}}$	25	Amps
Peak Non-Repetitive Surge Current (One Cycle, 60Hz)	I_{TSM}	250	Amps
Circuit Fusing Considerations $t = 1\text{ms}$ $t = 8.3\text{ms}$	I^2t	150 260	A^2s
Peak Gate Power (Pulse Width = 10μs)	P_{GM}	10	Watts
Average Gate Power	$P_{\text{G(AV)}}$	0.5	Watt
Peak Gate Power	I_{GM}	2	Amps
Operating Junction Temperature Range	T_J	-40 to +115	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +125	$^\circ\text{C}$
Stud Torque	-	30	in. lb.

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction to Case SC260, SC261 SC260()3	$R_{\theta\text{JC}}$	1.8 1.95	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS

($T_C = 250^\circ\text{C}$ unless otherwise noted. Values apply for either polarity of Main Terminal 2. Characteristics referenced to Main Terminal 1)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Forward or Reverse Blocking Current (Rated V_{DRM} or V_{RRM} , gate open) $T_C = 25^\circ\text{C}$ $T_C = +115^\circ\text{C}$	$I_{\text{DRM}}, I_{\text{RRM}}$	- -	- -	10 1	μA mA
Peak On-State Voltage ($I_{\text{TM}} = 35\text{ A Peak}$, Pulse Width = 1 ms, Duty Cycle $\leq 2\%$)	V_{TM}	-	-	1.58	Volts
Critical Rate of Rise of Off-State Voltage (Rated V_{DRM} , Gate Open-Circuited, Exponential Waveform) $T_C = +115^\circ\text{C}$	dv/dt	50	-	-	$\text{V}/\mu\text{s}$
Critical Rate-of-Rise of Commutating Off-State Voltage ($I_{\text{T(RMS)}}$ = Rated RMS On-State Current, V_{DRM} = Rated Peak Off-State Voltage, Gate Open-Circuited, Commutating $di/dt = 13.5\text{ A/ms}$, $T_C = +80^\circ\text{C}$)	$dv/dt(c)$	5	-	-	$\text{V}/\mu\text{s}$
DC Gate Trigger Current (Continuous dc) ($V_D = 12\text{ Vdc}$) MT2(+), G(+); MT2(-), G(-); $R_L = 100\text{ Ohms}$ MT2(+), G(-); $R_L = 50\text{ Ohms}$	I_{GT}	- -	- -	50 50	mAdc
DC Gate Trigger Current (Continuous dc) ($V_D = 12\text{ Vdc}$, $T_C = -40^\circ\text{C}$) MT2(+), G(+); MT2(-), G(-); $R_L = 50\text{ Ohms}$ MT2(+), G(-); $R_L = 25\text{ Ohms}$	I_{GT}	- -	- -	80 80	mAdc

DIGITRON SEMICONDUCTORS

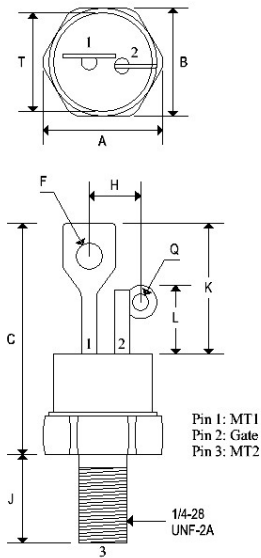
SC260, SC260Q3, SC261(MAC261) SERIES

THYRISTORS

Characteristic	Symbol	Min	Typ	Max	Unit
DC Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ Vdc}$) MT2(+), G(+); MT2(-), G(-); $R_L = 100 \text{ Ohms}$ MT2(+), G(-); $R_L = 50 \text{ Ohms}$	V_{GT}	—	—	2.5 2.5	Vdc
DC Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ Vdc}$, $T_C = -40^\circ\text{C}$) MT2(+), G(+); MT2(-), G(-); $R_L = 50 \text{ Ohms}$ MT2(+), G(-); $R_L = 25 \text{ Ohms}$	V_{GT}	-	-	3.5 3.5	Vdc
DC Gate Non-Trigger Voltage ($V_D = \text{Rated } V_{DRM}$, $R_L = 1k \text{ Ohms}$, $T_C = 115^\circ\text{C}$), all trigger modes	V_{GD}	0.25	-	-	Vdc
Holding Current ($V_D = 24 \text{ Vdc}$, Peak Initiating Current = 0.5 A, Pulse Width = 0.1 to 10 ms, Gate Trigger Source = 7 V, 20 Ohms $T_C = +25^\circ\text{C}$ $T_C = -40^\circ\text{C}$	I_H	-	-	75 100	mAdc
Latching Current ($V_D = 24 \text{ Vdc}$, Gate Trigger Source = 15 V, 100 Ohms, Pulse Width = 50 μs , 5 μs Maximum Rise and Fall Times) MT2(+), G(+); MT2(-), G(-), $T_C = 25^\circ\text{C}$ MT2(+), G(-), $T_C = 25^\circ\text{C}$ MT2(+), G(+); MT2(-), G(-), $T_C = -40^\circ\text{C}$ MT2(+), G(-), $T_C = -40^\circ\text{C}$	I_L	-	-	100 200 200 400	mAdc

MECHANICAL CHARACTERISTICS

Case	TO-48 (SC260 Series)
Marking	Alpha-numeric
Polarity	Cathode is stud



	TO-48			
	Inches		Millimeters	
	Min	Max	Min	Max
A	0.604	0.614	15.340	15.600
B	0.551	0.559	14.000	14.200
C	1.050	1.190	2.670	30.230
F	0.135	0.160	3.430	4.060
H	-	0.265	-	6.730
J	0.420	0.455	10.670	11.560
K	0.620	0.670	15.750	17.020
L	0.300	0.350	7.620	8.890
Q	0.055	0.085	1.400	2.160
T	0.501	0.505	12.730	12.830

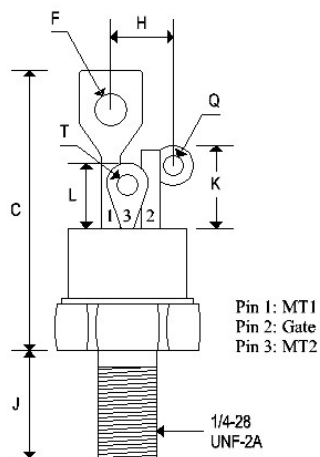
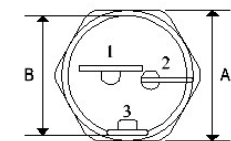
DIGITRON SEMICONDUCTORS

SC260, SC260()3, SC261(MAC261) SERIES

THYRISTORS

MECHANICAL CHARACTERISTIC

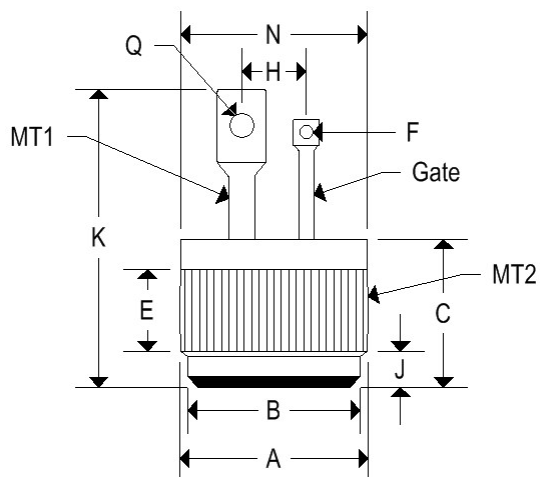
Case	TO-48 ISO (SC260()3 Series)
Marking	Alpha-numeric
Polarity	Cathode is stud



	TO-48 ISO			
	Inches		Millimeters	
	Min	Max	Min	Max
A	0.551	0.559	14.000	14.200
B	0.501	0.505	12.730	12.830
C	-	1.280	-	32.510
F	-	0.160	-	4.060
H	-	0.265	-	6.730
J	0.420	0.455	10.670	11.560
K	0.300	0.350	7.620	8.890
L	0.255	0.275	6.480	6.990
Q	0.055	0.085	1.400	2.160
T	0.135	0.150	3.430	3.810

MECHANICAL CHARACTERISTIC

Case	Digi PF1 (SC261(MAC261) Series)
Marking	Alpha-numeric



	DIGI PF1			
	Inches		Millimeters	
	Min	Max	Min	Max
A	0.501	0.505	12.730	12.830
F	-	0.160	-	4.060
G	0.085	0.095	2.160	2.410
H	0.060	0.070	1.520	1.780
J	0.300	0.350	7.620	8.890
K	-	1.050	-	26.670
L	-	0.670	-	17.020
Q	0.055	0.085	1.400	2.160

DIGITRON SEMICONDUCTORS

SC260, SC260Q3, SC261(MAC261) SERIES

THYRISTORS

FIGURE 1 – CURRENT DERATING

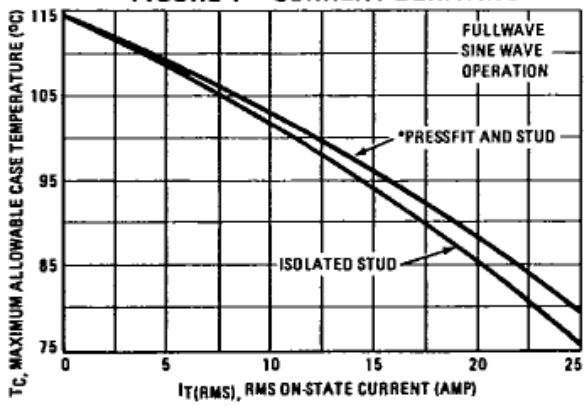


FIGURE 2 – MAXIMUM ON-STATE POWER DISSIPATION

